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Docket No.: M4065.0959/P959  
(PATENT)

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of:  
Dean A. Klein

Application No.: 10/796,111

Confirmation No.: 2460

Filed: March 10, 2004

Art Unit: 2818

For: POWER MANAGEMENT CONTROL  
AND CONTROLLING MEMORY  
REFRESH OPERATIONS

Examiner: Not Yet Assigned

**INFORMATION DISCLOSURE STATEMENT (IDS)**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 CFR 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is filed within three months of the U.S. filing date (37 CFR 1.97(b)(1)).

Pursuant to United States Patent and Trademark Office Official Gazette Notice: 05 August 2003 ("Information Disclosure Statements May Be Filed Without Copies of U.S. Patents and Published Applications in Patent Applications filed after June 30, 2003") copies of the U.S. Patent Document references (i.e., references AA-AU7 ) on the PTO/SB/08 are not provided. Copies of the Foreign Patent Document references (i.e.,

references BA, BB, and BC) and the Other Prior Art – Non Patent Literature Document References (i.e., references CA – CO6) on the PTO/SB/08 are provided.

In accordance with 37 CFR 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 CFR 1.56(a) exists. In accordance with 37 CFR 1.97(h), the filing of this Information Disclosure statement shall not be construed to be an admission that any patent, publication or other information referred to therein is “prior art” for this invention unless specifically designated as such.

It is submitted that the Information Disclosure Statement is in compliance with 37 CFR 1.98 and the Examiner is respectfully requested to consider the listed references.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0959/P959. A duplicate copy of this paper is enclosed.

Dated: June 10, 2004

Respectfully submitted,

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PTO/SB/08A (10-01)

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U. S. Patent and Trademark Office: U. S. DEPARTMENT OF COMMERCE

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Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>				<b>Complete if Known</b>	
				Application Number	10/796,111
				Filing Date	March 10, 2004
				First Named Inventor	Dean A. Klein
				Art Unit	2818
				Examiner Name	Not Yet Assigned
Sheet	1	of	13	Attorney Docket Number	M4065.0959/P0959

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
	AA	2002/0000666	1/2002	Kozicki et al.	
	AB	2002/0072188	6/2002	Gilton	
	AC	2002/0106849	08/2002	Moore	
	AD	2002/0123169	09/2002	Moore et al.	
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	AP1	4,269,935	5/1981	Masters et al.	
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Sheet	2	of	13	Attorney Docket Number	M4065.0959/P0959

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Sheet	3	of	13	Attorney Docket Number	M4065.0959/P0959

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	AQ3	6,469,364	10/2002	Kozicki	
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Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>				<b>Complete if Known</b>	
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Sheet	4	of	13	Attorney Docket Number	M4065.0959/P0959

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Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>				<b>Complete if Known</b>	
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Sheet	5	of	13	Attorney Docket Number	M4065.0959/P0959

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Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				
	BA	JP	56126916	10/1981	Akira et al.		
	BB	WO	97/48032	12/18/1997	Kozicki et al.		
	BC	WO	99/28914	06/10/1999	Kozicki et al.		
Examiner Signature					Date Considered		

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See attached Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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Substitute for form 1449B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)				<b>Complete if Known</b>	
				Application Number	10/618,824
				Filing Date	July 14, 2003
				First Named Inventor	Terry L. Gilton
				Group Art Unit	N/A
				Examiner Name	Not Yet Assigned
Sheet	6	of	13	Attorney Docket Number	M4065.1006/P1006-A

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	CA	Abdel-Ail, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge <sub>5</sub> As <sub>38</sub> Te <sub>57</sub> chalcogenide glass, Vacuum 59 (2000) 845-853.	
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	CD	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se <sub>75</sub> Ge <sub>25</sub> -xSbx, Appl. Phys. A 55 (1992) 167-169.	
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	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.	
	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.	
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	CL	Axon Technologies Corporation, TECHNOLOGY DESCRIPTION: <i>Programmable Metalization Cell(PMC)</i> , pp. 1-6 (Pre-May 2000).	
	CM	Baranovskii, S.D.; Cordes, H., On the conduction mechanism in ionic glasses, J. Chem. Phys. 111 (1999) 7546-7557.	
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				Application Number	10/618,824
				Filing Date	July 14, 2003
				First Named Inventor	Terry L. Gilton
				Group Art Unit	N/A
				Examiner Name	Not Yet Assigned
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Examiner Signature		Date Considered	
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